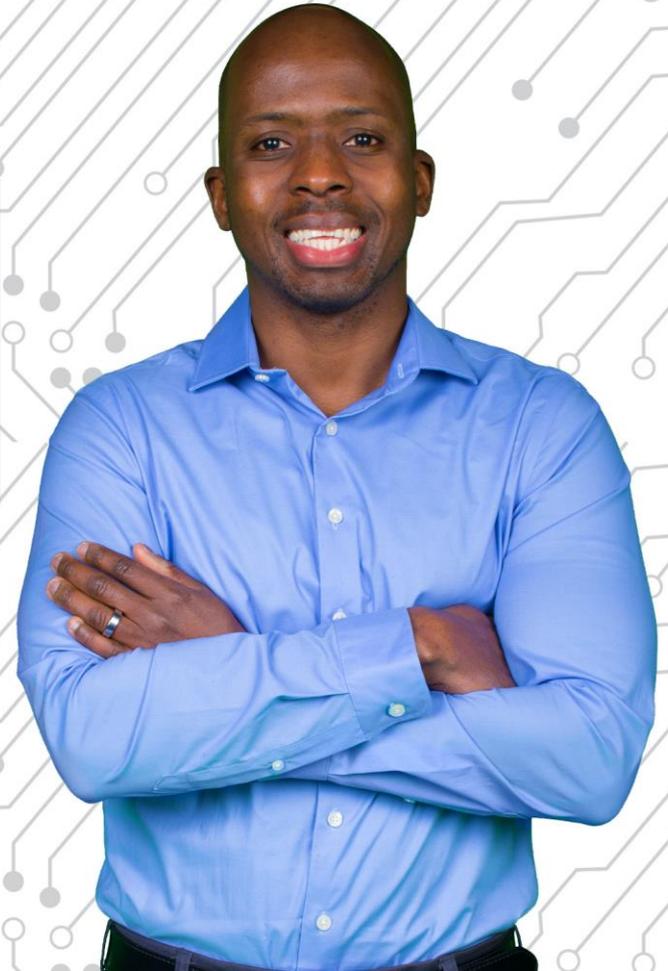


HIGH VOLTAGE SEMINAR

MAMADOU DIALLO

HIGH POWER GATE DRIVERS

TROUBLESHOOTING GATE DRIVE
CIRCUITS IN AUTOMOTIVE AND
INDUSTRIAL APPLICATIONS



Acknowledgement

Jeff Mueller

Richard Herring

Derek Payne

Mateo Begue

Ritesh Oza

Wei Zhang

Don Dapkus

What will I get out of this session?

Purpose:

- **Gate driver Fundamentals**
- **Common issues, solutions and design practices on:**
 1. Bias/bootstrap supply
 2. Open functional pins or connect with Hi-Z
 3. Parasitics
 4. dv/dt noise
 5. Variance

Part numbers mentioned:

- UCC27282
- UCC27710
- UCC27284-Q1
- UCC27201
- UCC27524

Relevant applications:

- Motor drive
- Switch mode power supplies
- Solar inverters

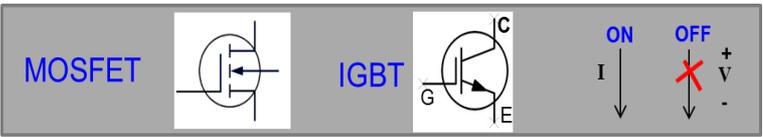
Where are gate drivers used?



Fundamental Component in Power Electronics

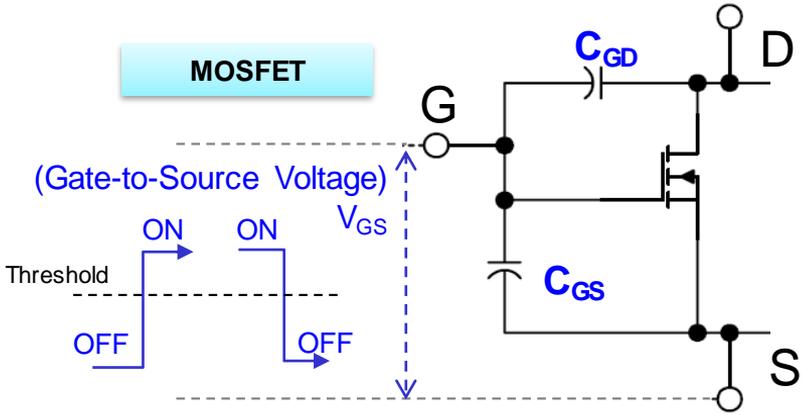


Power Switches control flow of current in power electronic circuits by operating in 2 states (ON/OFF)



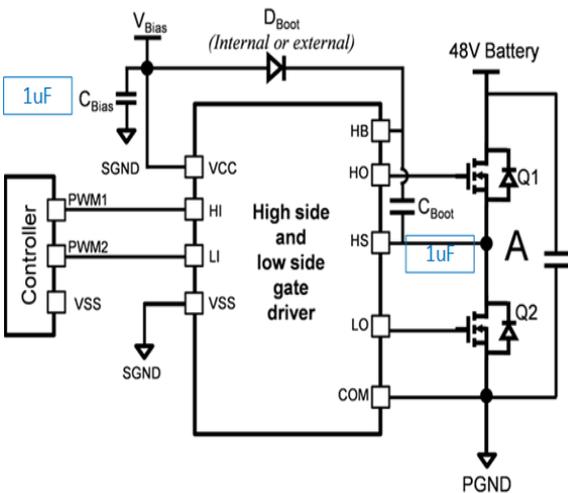
GATE (G) terminal controls ON/OFF status of switch

Si → GaN and SiC



To turn ON: Apply a positive voltage, $V_{GS} >$ Threshold level
To turn OFF: $V_{GS} <$ Threshold level

#1 What is wrong with VCC?

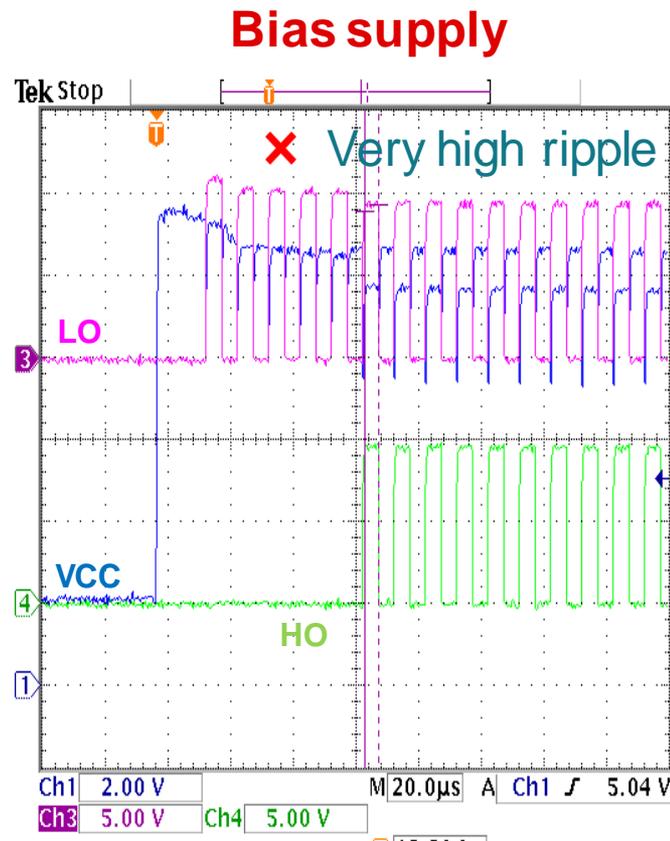


Causes

- Low capacitance on V_{CC}
- Capacitor placement/layout
- Biased capacitance (C vs. V)
- Temperature (C vs. temp)
- Capacitance aging

Consequences

- ✗ Driver malfunction
- ✗ UVLO tripping
- ✗ EMI noise



#1 VCC bias capacitor considerations

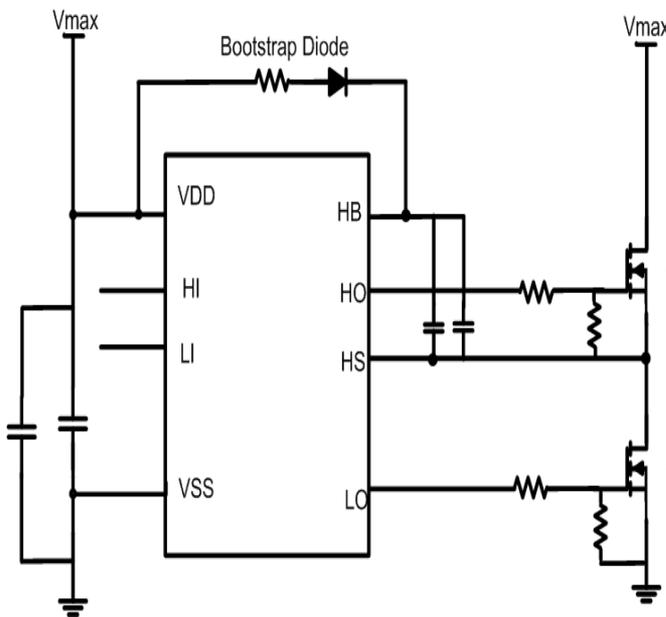
- Increase VCC bias capacitor
- Rule of Thumb: $C_{VCC} \geq 10 \times C_{boot}$
- Place the VCC bias capacitor very close to the VCC pin of the driver

Sizing VCC bypass capacitor

- $\Delta V_{HB} = V_{CC} - V_{DF} - V_{HBL}$
- $C_{BOOT} = Q_{Total} / \Delta V_{HB}$
- $C_{Bias} \gg C_{Boot}$
- High freq. filter capacitor

What is wrong with HO waveform?

Bias supply



- Causes:
 - Low capacitance
 - Low R_{gs}
 - Low F_{sw}
 - Large D
- Consequences
 - ✗ Hot MOSFET
 - ✗ Output ripple



✗ HO drooping /
Bootstrap leakage

#2 bootstrap capacitor considerations

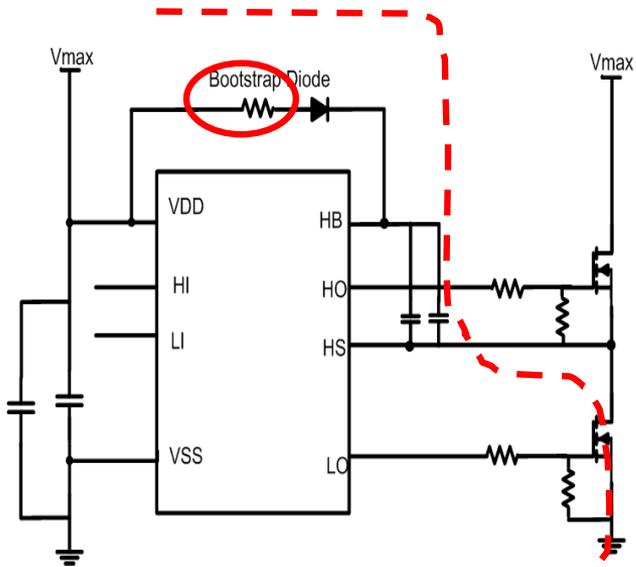
- Increase Cboot
- Increase Rgs
- Place the boot capacitor very close to the HB-HS pins of the driver

Sizing bootstrap capacitor

- $C_{\text{Boot}} = Q_{\text{Total}} / \Delta V_{\text{HB}}$
- $Q_{\text{Total}} = Q_{\text{G}} + (I_{\text{HBS}} \times D_{\text{Max}} / F_{\text{SW}}) + (I_{\text{HB}} / F_{\text{sw}})$

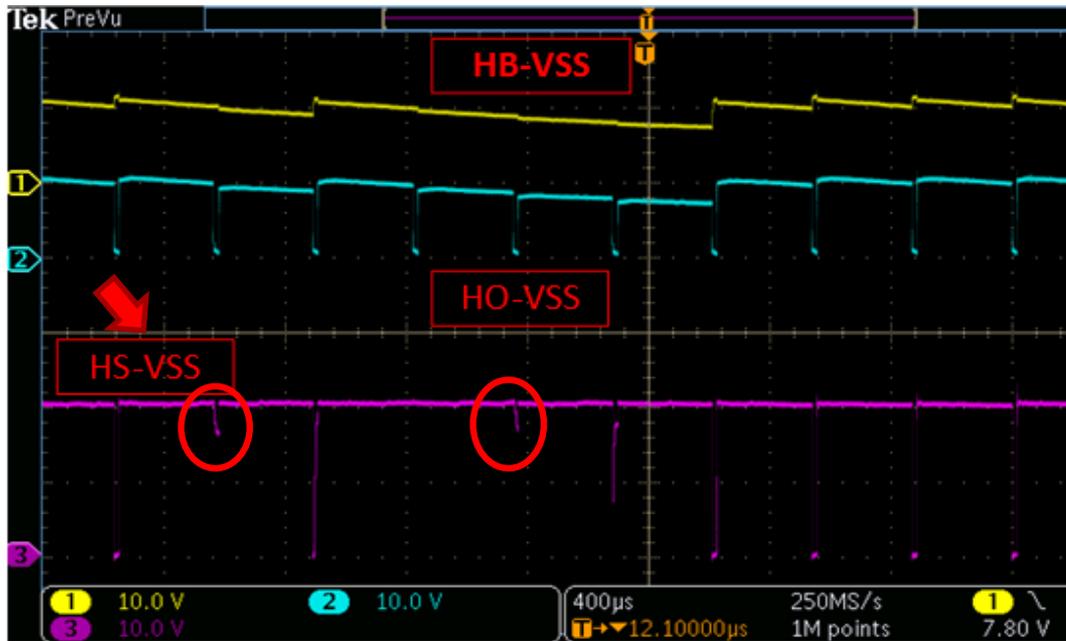
#2 What is wrong with switch node waveform?

Bias supply



Design guidelines

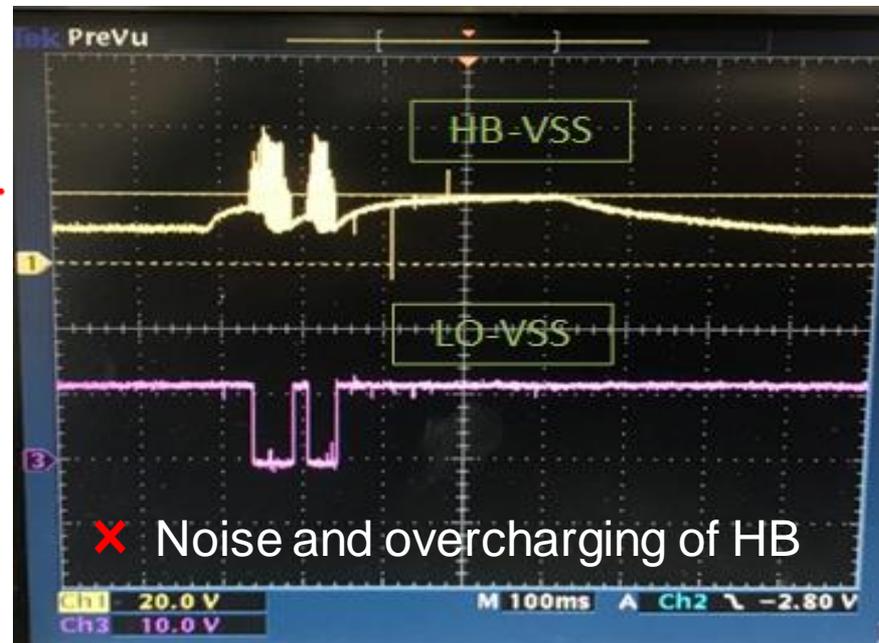
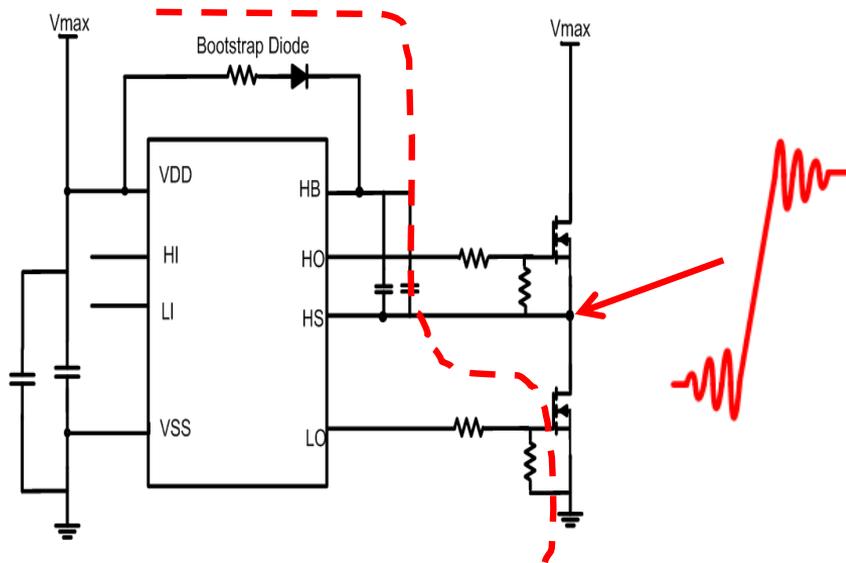
- Reduce R_{Boot}
- Minimum top switch ON time



- ✗ HS waveform – inconsistent HS signal
- ✗ Very short LO duty cycle – partially charged C_{Boot}

#3 Is this waveform normal?

Bias supply



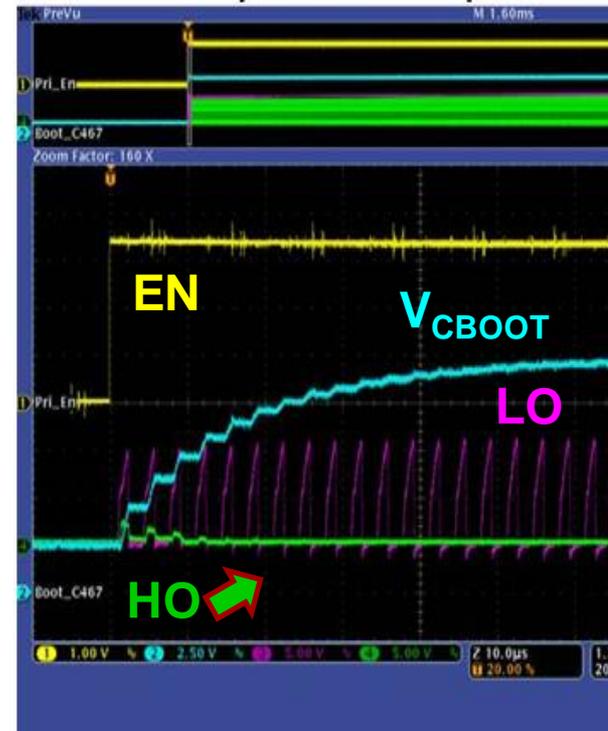
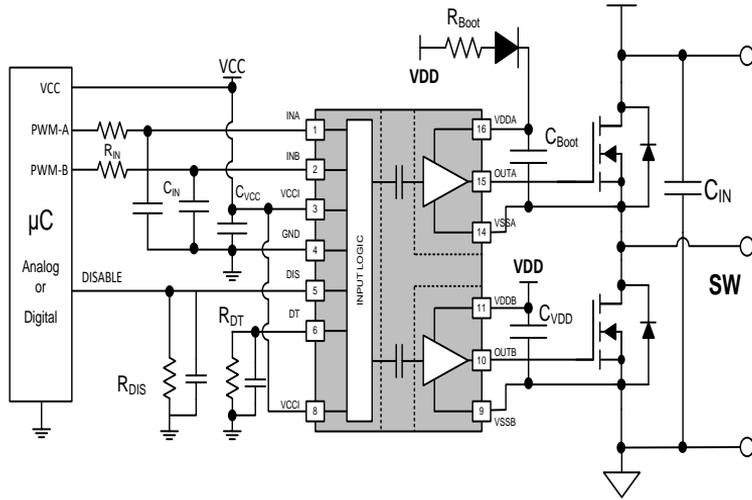
Design guidelines

- Increase boot resistor
- Increase boot capacitor

- ✗ HS neg. ringing → overcharging the boot cap
- ✗ Fast HS slew rate → noise and oscillation on HB

#4 Why is there NO gate driver output?

Bias supply



- High side boot supply is ready
- Driver IC is enabled
- PWM input HI&LI are ready
- The low side LO is good

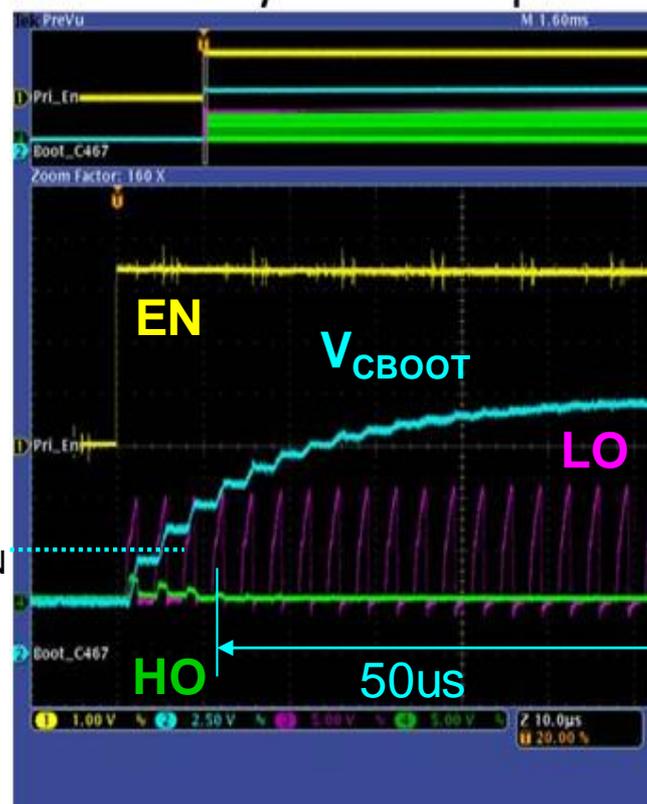
#4 Why is there NO gate driver output?

Bias supply

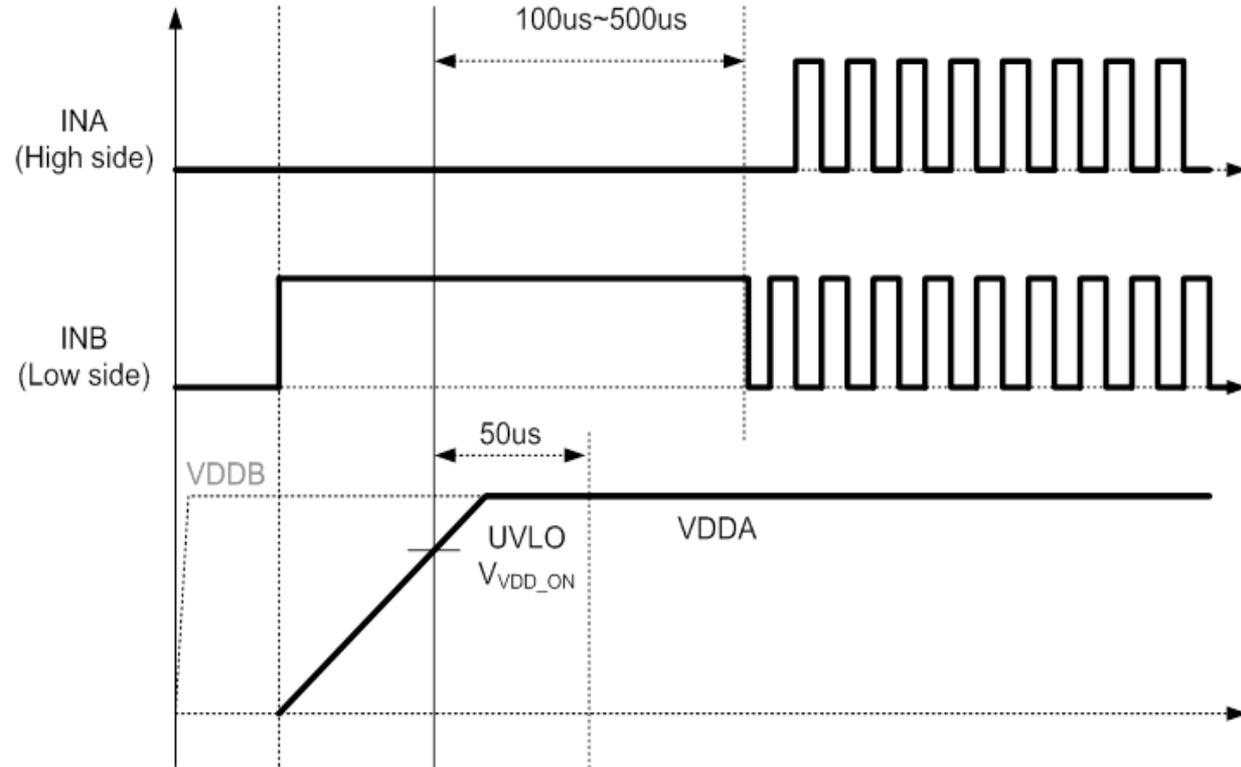
- High side boot supply is ready
- Driver IC is enabled
- PWM input HI&LI are ready
- The low side LO is good

✗ There is NO high side output

- ❑ **UVLO delay:** 5 μ s to 100 μ s depends on the driver



Bias supply



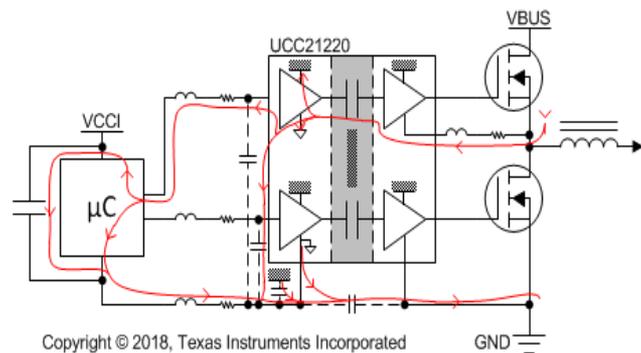
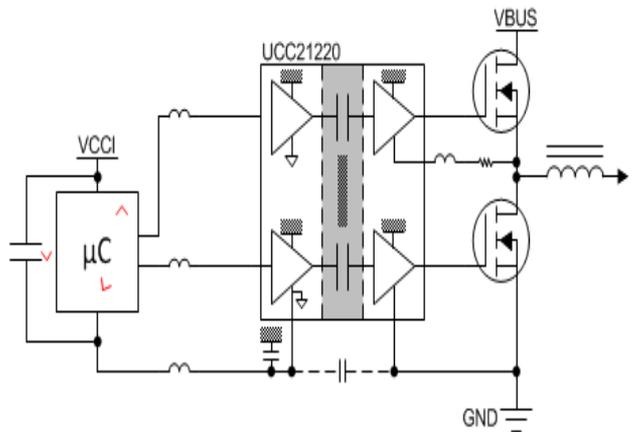
Design guidelines

- Turn-on low side to pre-charge boot capacitor
- Synchronize HI and LI

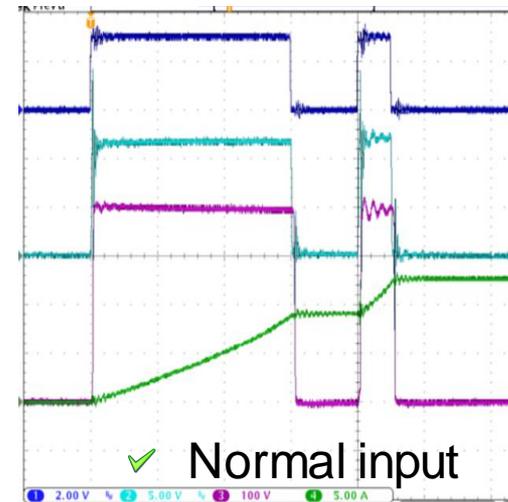
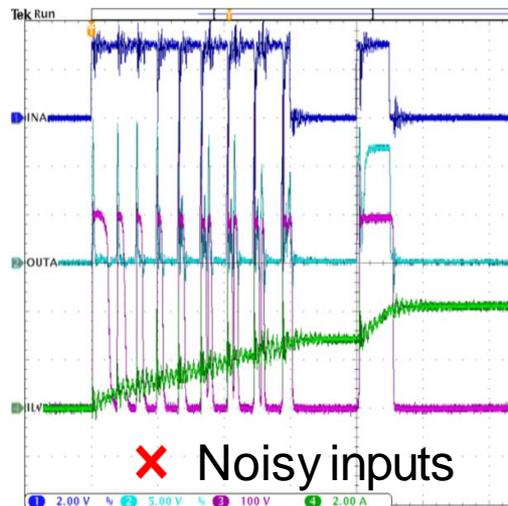
Synchronization LI and HI after bias supplies are both ready

#5 What is wrong with the waveform?

Pin w/ Hi-Z



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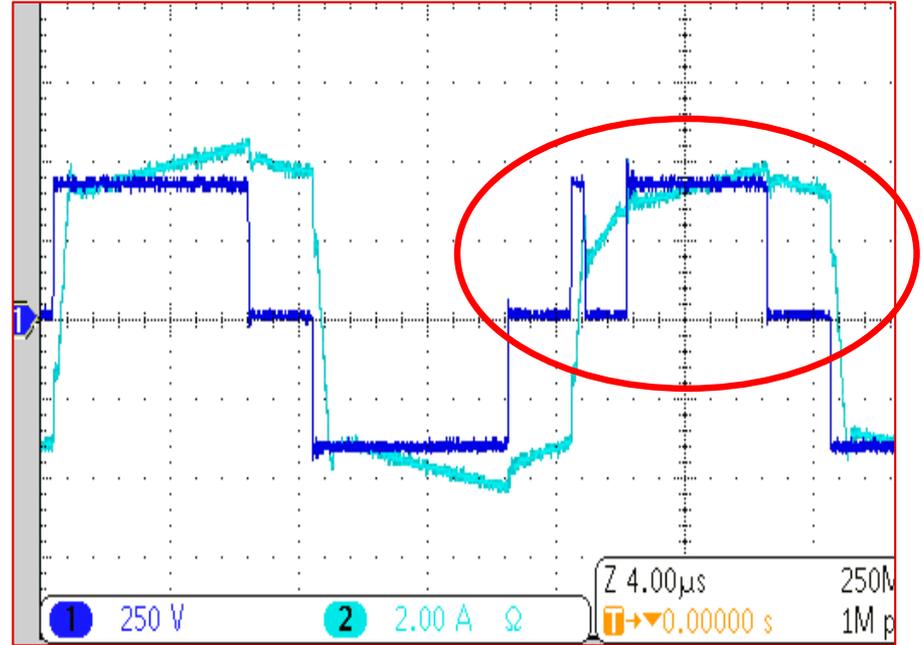
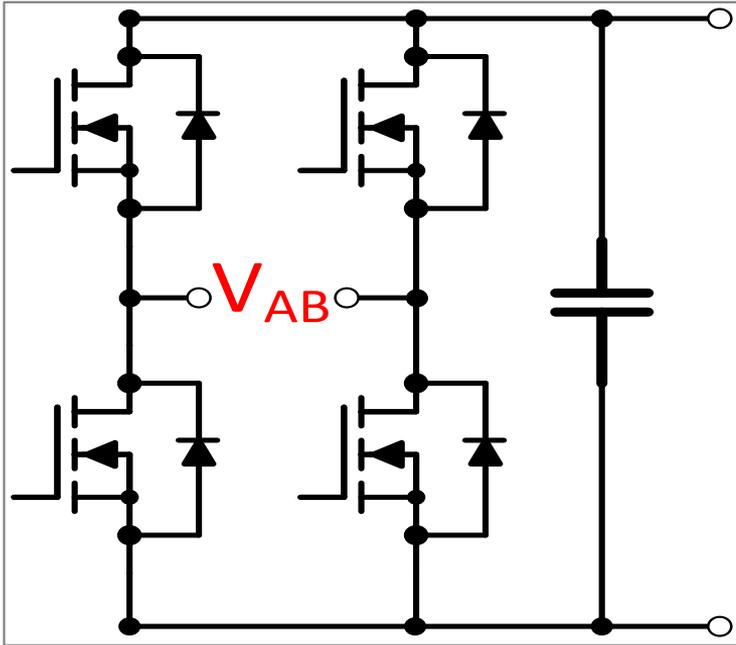


Design guidelines:

- Input filter to improve overall system performance
- Decrease loop inductance in PCB layout

#6 What causes glitches in PSFB at full load?

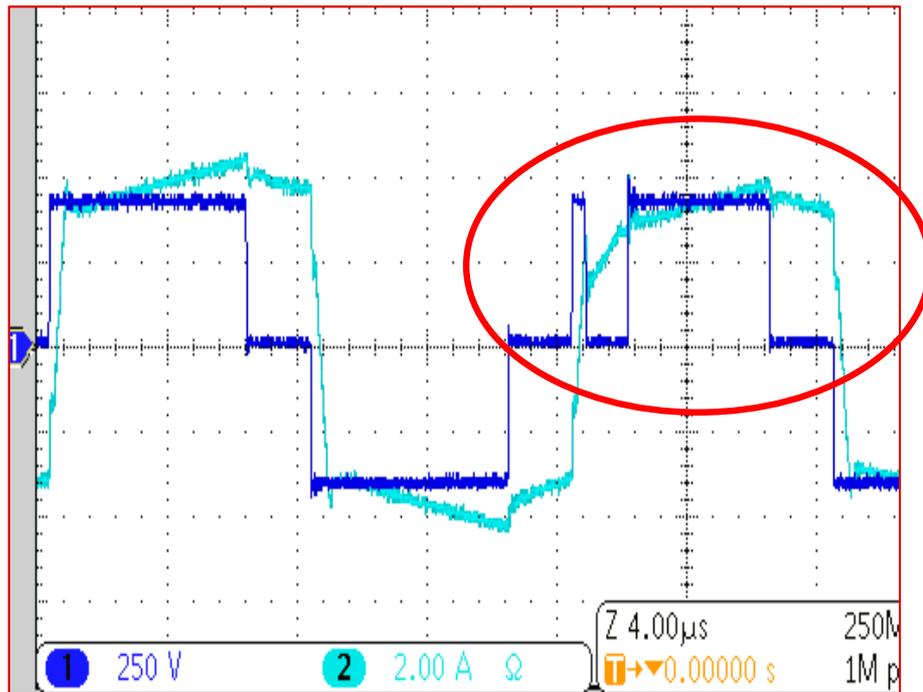
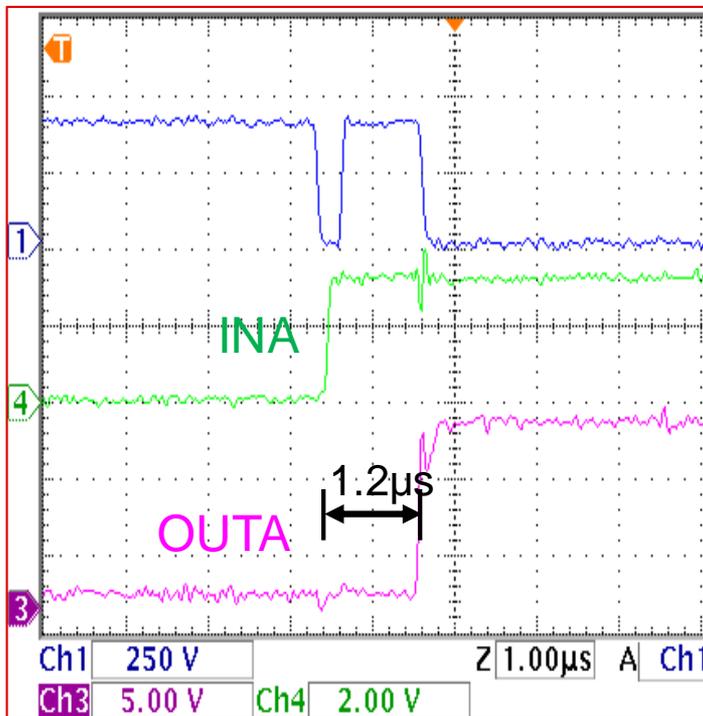
Pin w/ Hi-Z



✘ Voltage waveform “VAB” has intermittent failure and glitches

#6 What causes glitches in PSFB at full load?

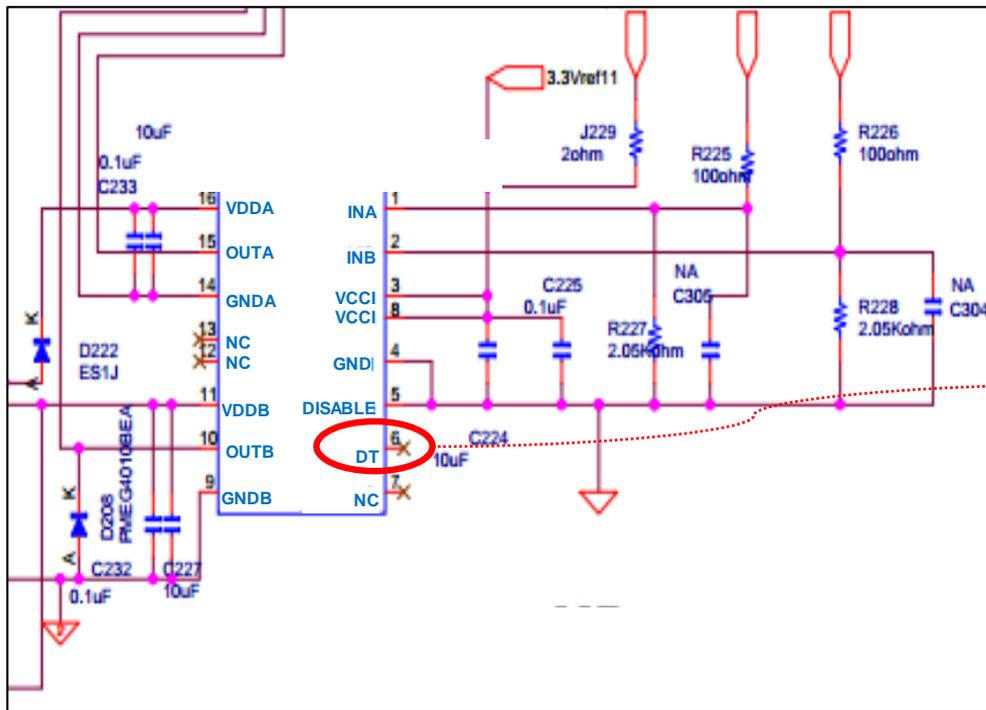
Pin w/ Hi-Z



✗ Output A is being delayed by 1.2µs (which should be <50ns)

Root cause

Pin w/ Hi-Z



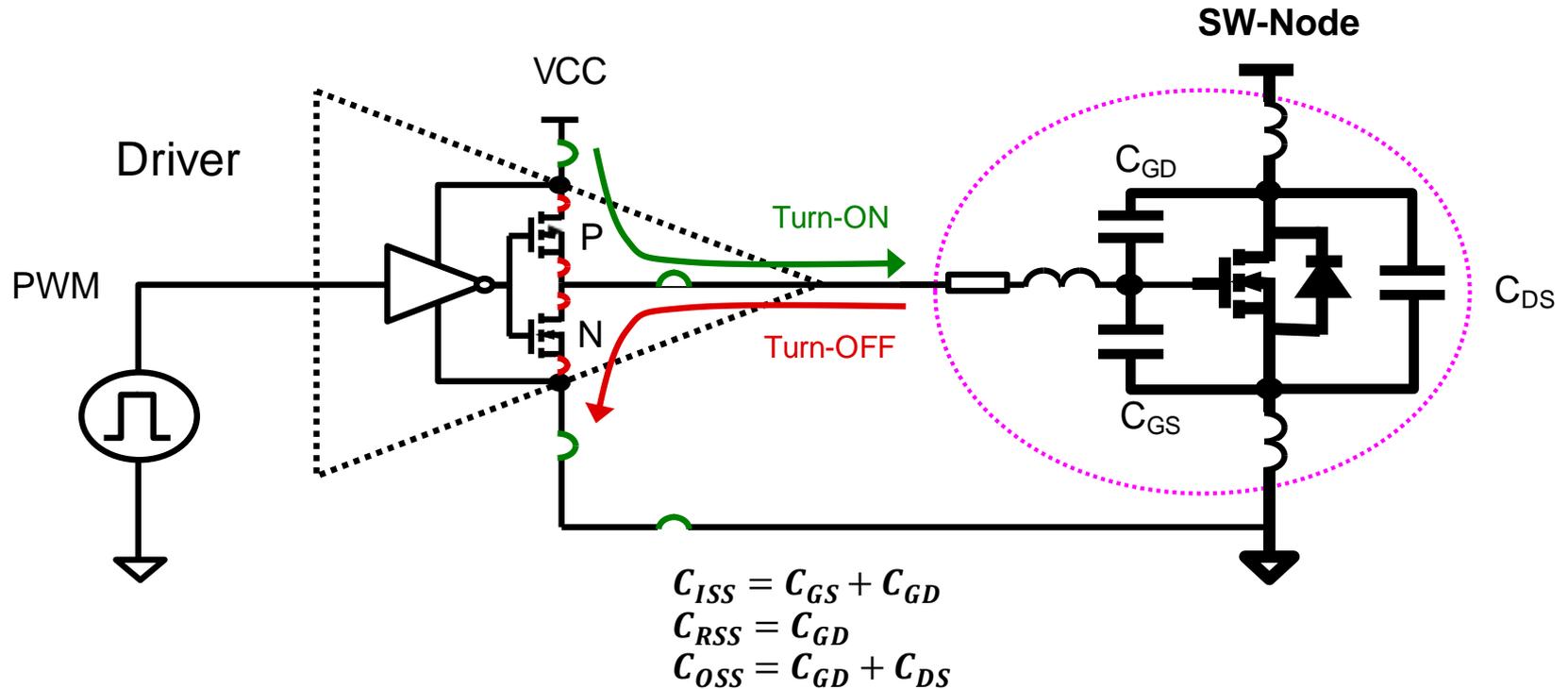
Design guidelines

- DT pin is left open and noise is coupled into the driver
- For dead time setting, bypass with $\geq 2.2\text{nF}$ close to DT pin
$$\text{DT (in ns)} = 10 \times \text{RDT (in k}\Omega\text{)}$$
- For overlapping or no DT, tie DT pin to VCCI

Do NOT leave functional pins open

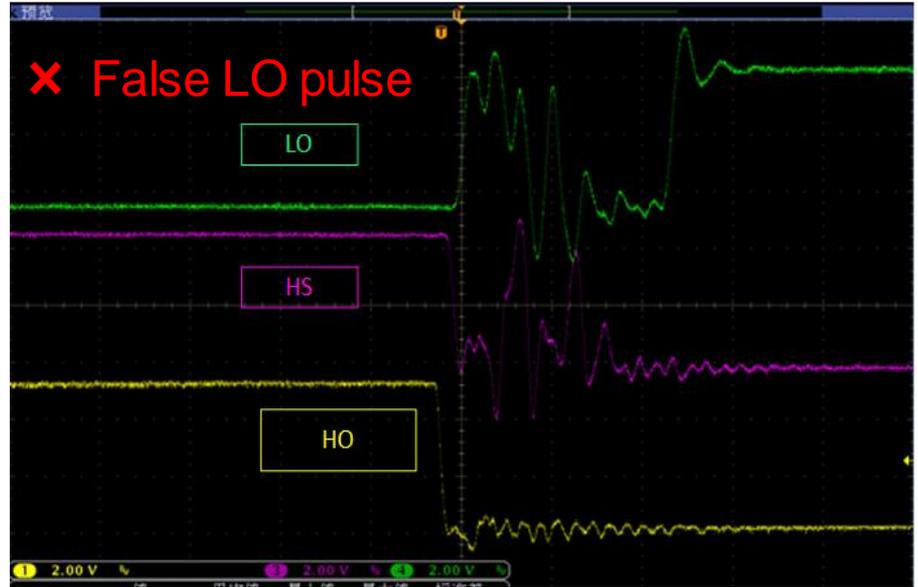
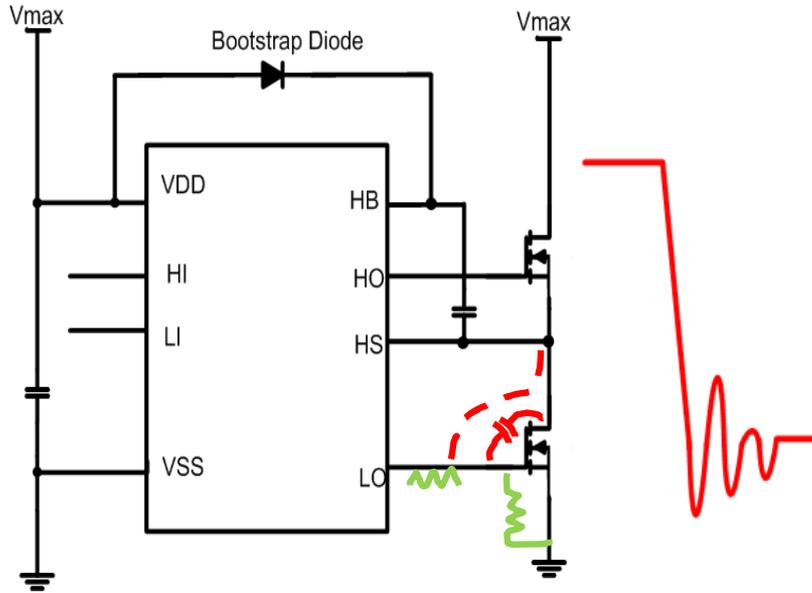
Parasitics in gate driver sub-system

Parasitics



#7 What Is wrong when HO turns off?

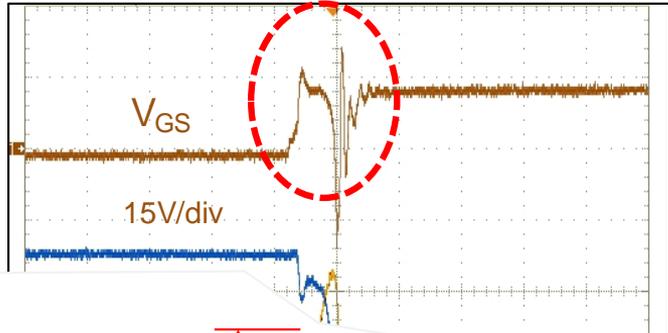
Parasitics



- High voltage and IGBT applications
- Series gate and gate to source resistor
- Driver with Miller clamp

- ✗ High dV/dt and dI/dt causes D-G capacitor to charge and develop voltage
- ✗ Voltage may be higher than $V_{gs(th)}$

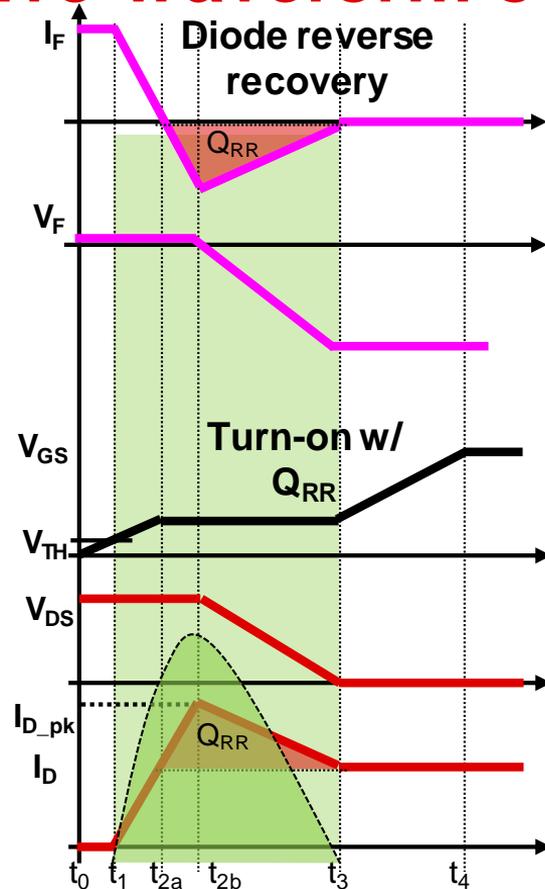
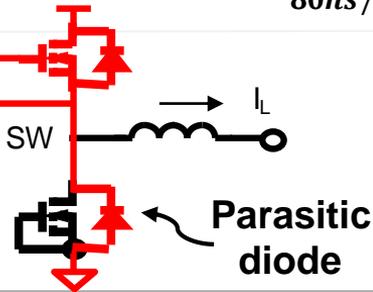
#8 Why is the gate drive waveform oscillating?



V_{DS} 100V/div

80ns/div

H-bridge
gate driver

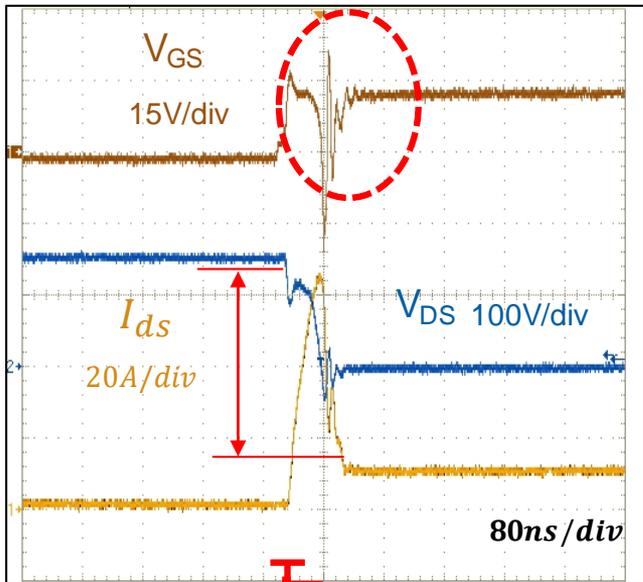


Parasitics

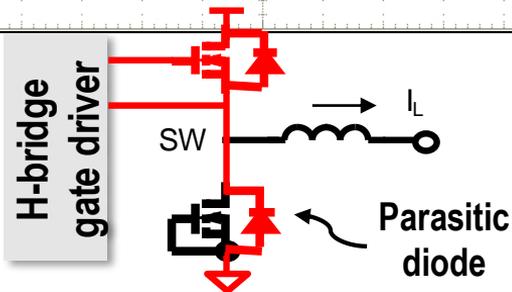
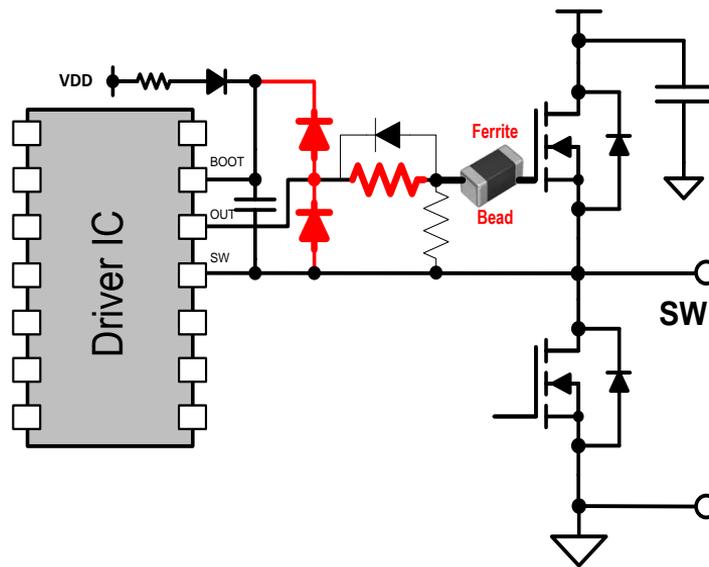
- ✗ Increase turn-on loss
- ✗ Higher di/dt, EMI
- ✗ Device overshoot
- ✗ Gate drive oscillation (over/under shoot)

#8 Why is the gate drive waveform oscillating?

Parasitics

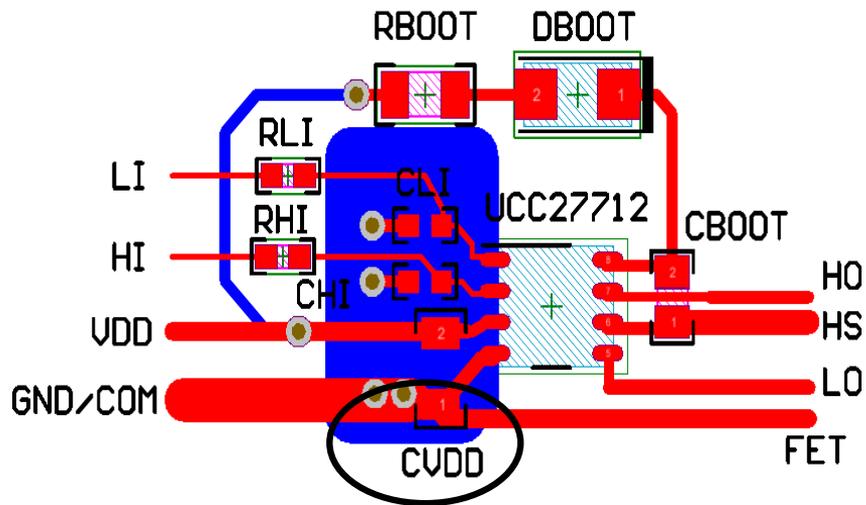


- Slow down body diode reverse recovery
- FET with robust and low Q_{RR} body diode
- Soft switching - ZVS

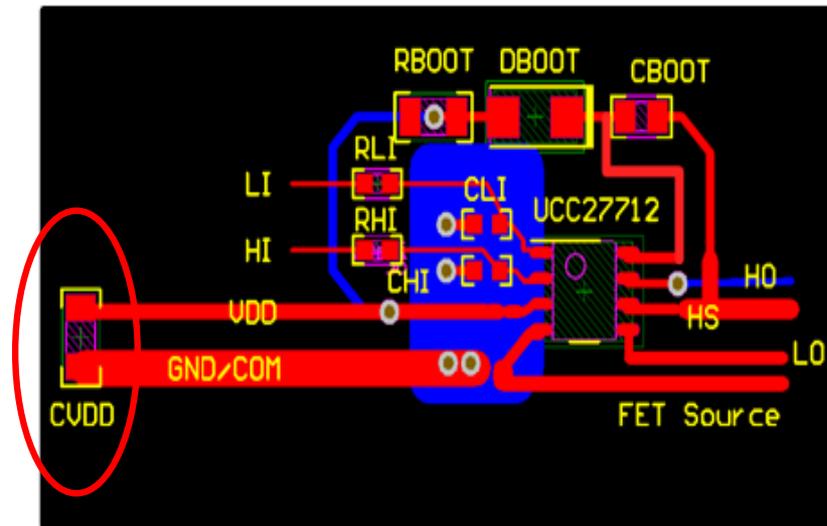


Examples

GOOD



BAD



- Bypass capacitor needs to be as close to gate driver IC as possible
- V_{CC} , V_{DD} , input filter, DT, EN, DIS
- Value and package of the capacitor do matter

#9 What is wrong with my HO output?

dv/dt

- Case 1: output is shorter than input

✗ HO 80ns glitches at HI=high

- Double pulse on HI
- LI pulled down w/ 4.7k Ω

HI (5V/div),
BW=1GHz

HO (10V/div),
BW=200MHz

HS(V_{DS-Low})
(50V/div)
BW=1GHz

I_L (5A/div)
(BW=120MHz)



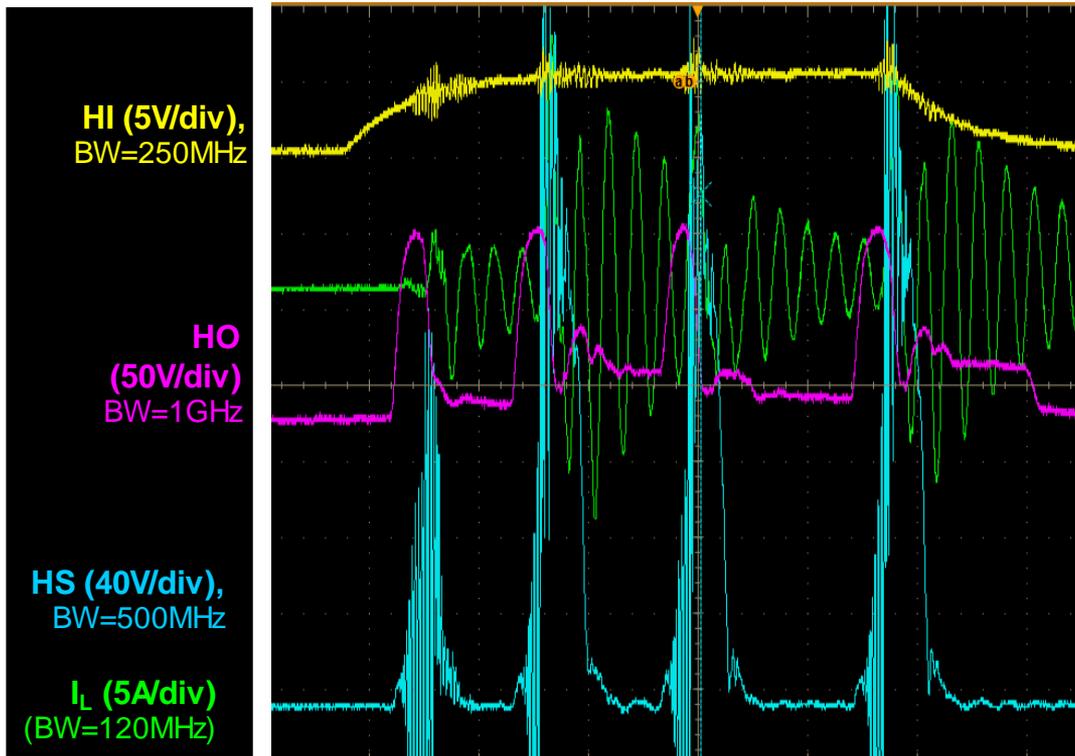
#9 What is wrong with my output?

dv/dt

- Case 3: output on and off intermittent while HI is ON

✘ HO turns off intermittent

- Double pulse on HI
- LI pulled down w/ 4.7k Ω



The switch node CMTI is $>200\text{V/ns}$

dv/dt

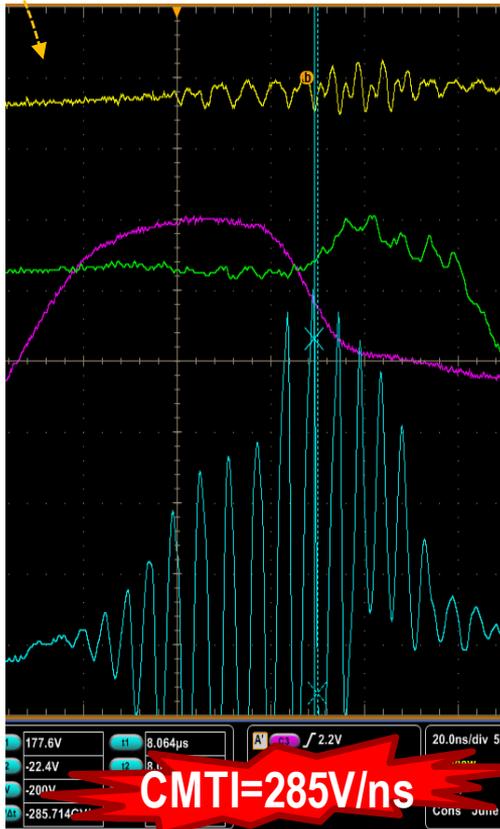
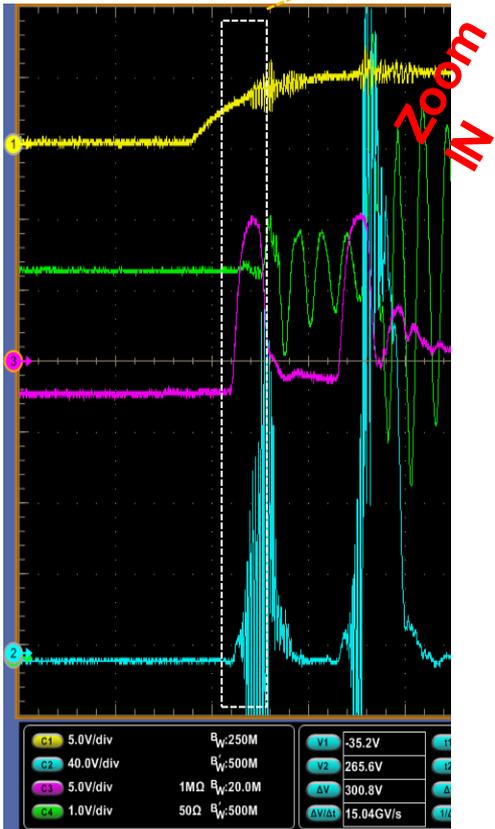
INA

I_L

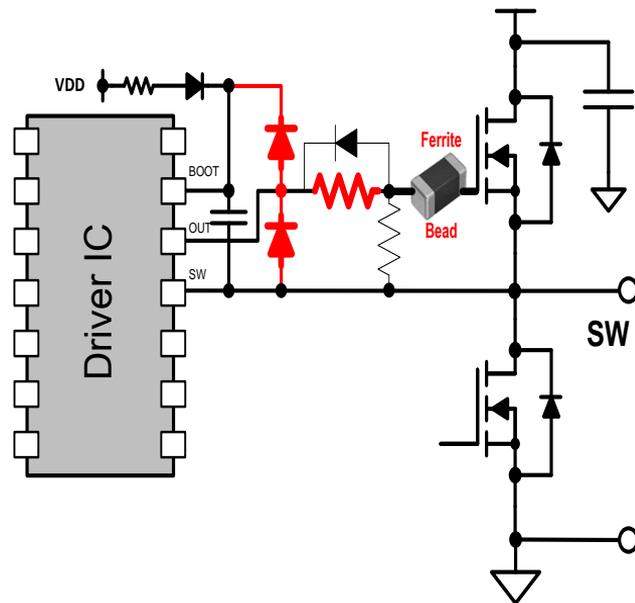
OUTA

SW

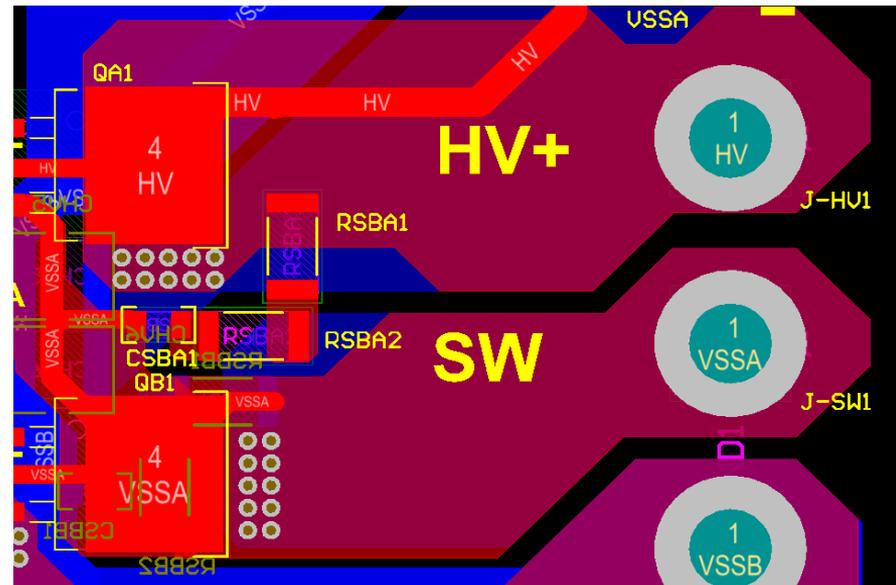
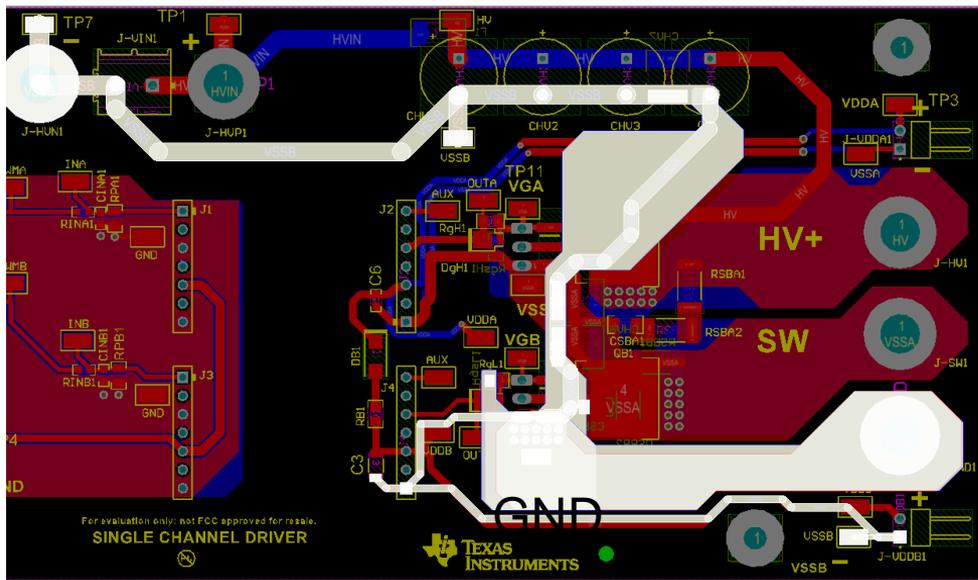
(500MHz)



- Slow down reverse recovery
- FET w/ low Q_{RR} B-diode
- Soft switching - ZVS



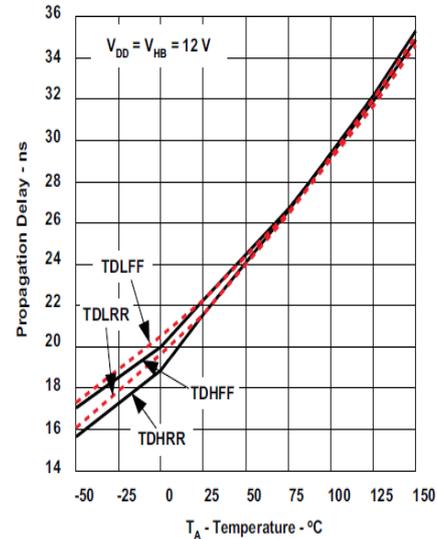
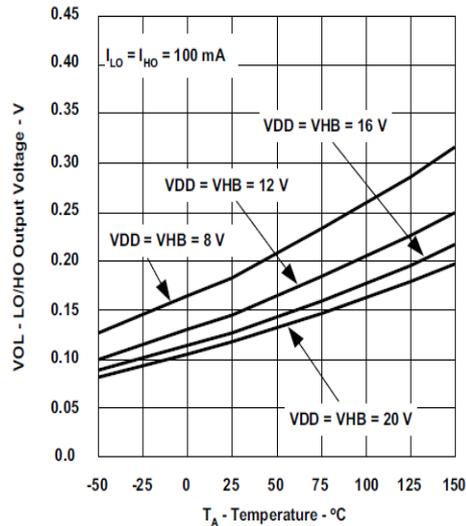
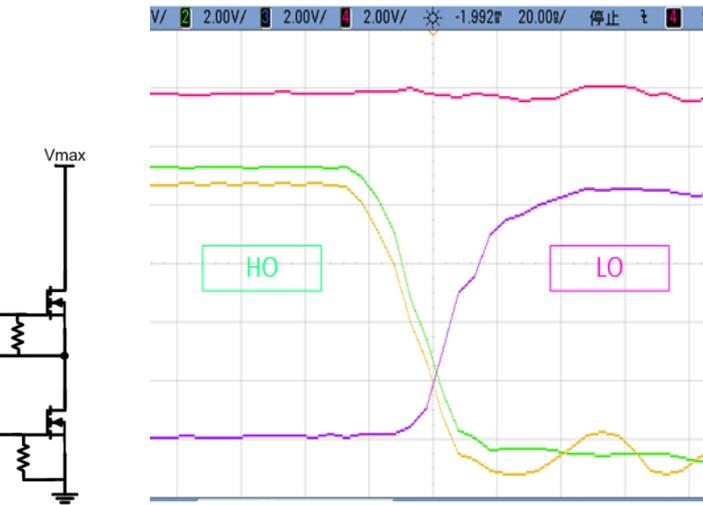
Layout: ground plane and switch node (SW) dv/dt



- Minimize or avoid overlapping switch node plane and ground plane
- Could create issues when switching frequencies are high
- As HS slew rates are high, overlap of ground plane and switch node plane might inject noise in other circuits on the board

#10 Would this waveform create any system problems?

Variance



✗ HO/LO might cross conduct

✗ Shoot-through current

✗ Excessive power dissipation

✗ False overcurrent tripping

- Account for propagation delay and delay matching variation across temperature/voltage
- Account for drive strength variation across temperature/bias voltage

Summary

- Various issues encountered while designing switch-mode power supplies were discussed from the gate driver IC point of view and their resolutions were clearly identified
- Proper bypassing of the gate driver IC (as with many other ICs) is extremely critical to its performance
- When gate driver IC is used in half-bridge configuration, switch node slew rate plays an important role in the performance of the gate driver IC
- PCB layout plays important role in satisfactory performance of the gate driver IC and thus the whole system



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